

2N7002L

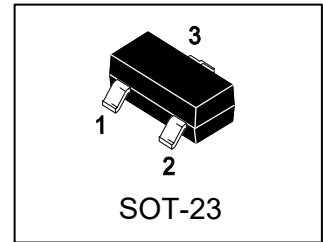
S-2N7002L

Small Signal MOSFET

115 mAmps, 60 Volts N-Channel SOT-23

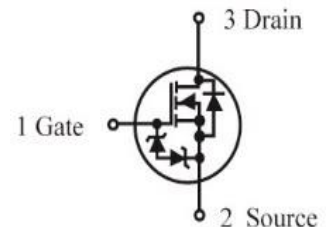
1. FEATURES

- We declare that the material of product compliance with RoHS requirements and Halogen Free.
- S- prefix for automotive and other applications requiring unique site and control change requirements; AEC-Q101 qualified and PPAP capable.
- ESD Protected:1000V



2. DEVICE MARKING AND ORDERING INFORMATION

Device	Marking	Shipping
2N7002L	702	3000/Tape&Reel



3. MAXIMUM RATINGS(Ta = 25°C)

Parameter	Symbol	Limits	Unit
Drain-Source Voltage	VDSS	60	V
Drain-Gate Voltage (RGS = 1.0 MΩ)	VDGR	60	V
Drain Current	ID		mA
- Continuous TC = 25°C		±115	
TC = 100°C		±75	
- Pulsed (Note 1)	IDM	±800	
Gate-Source Voltage			
- Continuous	VGS	±20	V
- Non-repetitive (tp ≤ 50μs)	VGSM	±40	V

4. THERMAL CHARACTERISTICS

Parameter	Symbol	Limits	Unit
Total Device Dissipation, FR-5 Board (Note 2) @ TA = 25°C Derate above 25°C	PD	225	mW
		1.8	mW/°C
Thermal Resistance, Junction-to-Ambient(Note 2)	ROJA	556	°C/W
Junction and Storage temperature	TJ,Tstg	-55~+150	°C

1. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

2. FR-5 = 1.0×0.75×0.062 in.



5. ELECTRICAL CHARACTERISTICS (Ta= 25°C)

OFF CHARACTERISTICS

Characteristic	Symbol	Min.	Typ.	Max.	Unit
Drain–Source Breakdown Voltage (VGS = 0, ID = 10μA)	VBRDSS	60	-	-	V
Zero Gate Voltage Drain Current TJ = 25°C (VGS = 0, VDS = 60 V) TJ = 125°C	IDSS	-	-	1.0	μA
		-	-	500	
Gate–Body Leakage Current, Forward (VGS = 20 V)	IGSSF	-	-	1.0	μA
Gate–Body Leakage Current, Reverse (VGS = - 20 V)	IGSSR	-	-	-1.0	μA

ON CHARACTERISTICS (Note 3)

Gate Threshold Voltage (VDS = VGS, ID = 250μA)	VGS(th)	1.0	1.6	2.0	V
On–State Drain Current (VDS ≥ 2.0 VDS(on), VGS = 10 V)	ID(on)	500	-	-	mA
Static Drain–Source On–State Voltage (VGS = 10 V, ID = 500 mA) (VGS = 5.0 V, ID = 50 mA)	VDS(on)	-	-	3.75	V
		-	-	0.375	
Static Drain–Source On–State Resistance (VGS = 10 V, ID = 500 mA) TC = 25°C TC = 125°C (VGS = 5.0 V, ID = 50 mA) TC = 25°C TC = 125°C	RDS(on)	-	-	7.5	Ohms
		-	-	13.5	
		-	-	7.5	
		-	-	13.5	
Forward Transconductance (VDS ≥ 2.0 VDS(on), ID = 200 mA)	gfs	80	-	-	mmhos

DYNAMIC CHARACTERISTICS

Input Capacitance (VDS = 25 V, VGS = 0, f = 1.0 MHz)	Ciss	-	17	50	pF
Output Capacitance (VDS = 25 V, VGS = 0, f = 1.0 MHz)	Coss	-	10	25	pF
Reverse Transfer Capacitance (VDS = 25 V, VGS = 0, f = 1.0 MHz)	Crss	-	2.5	5.0	pF

SWITCHING CHARACTERISTICS

Turn-On Delay Time	(VDD = 25 V, ID = 500 mA, RG = 25Ω, RL = 50 Ω, Vgen = 10 V)	td(on)	-	7	20	ns
Turn-Off Delay Time		td(off)	-	11	40	

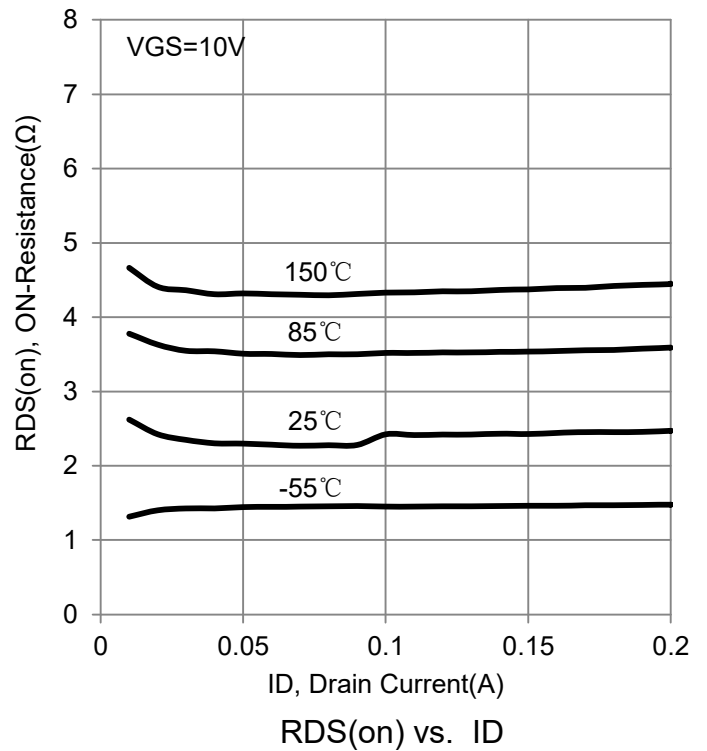
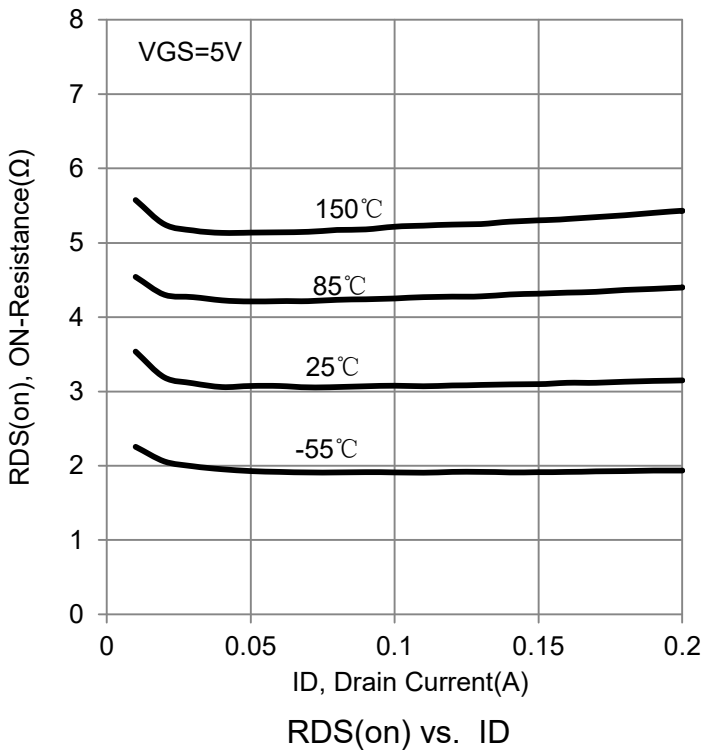
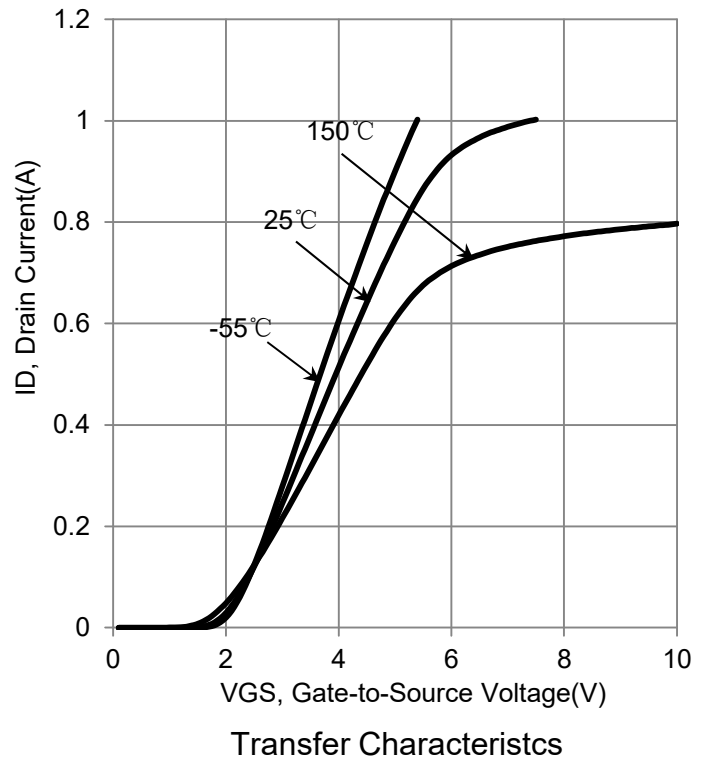
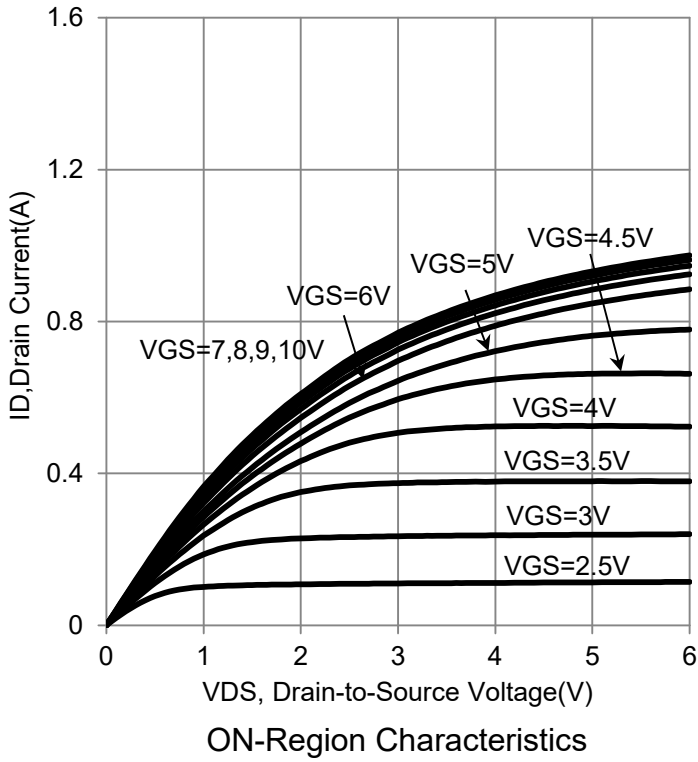
BODY–DRAIN DIODE RATINGS

Diode Forward On–Voltage (IS = 115 mA, VGS = 0 V)	VSD	-	-	1.5	V
Source Current Continuous (Body Diode)	IS	-	-	115	mA
Source Current Pulsed	ISM	-	-	800	mA

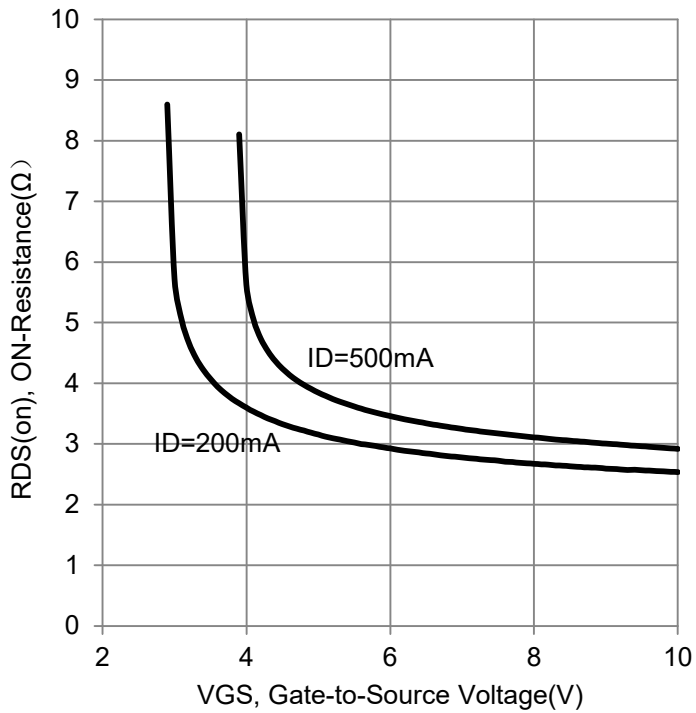
3.Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.



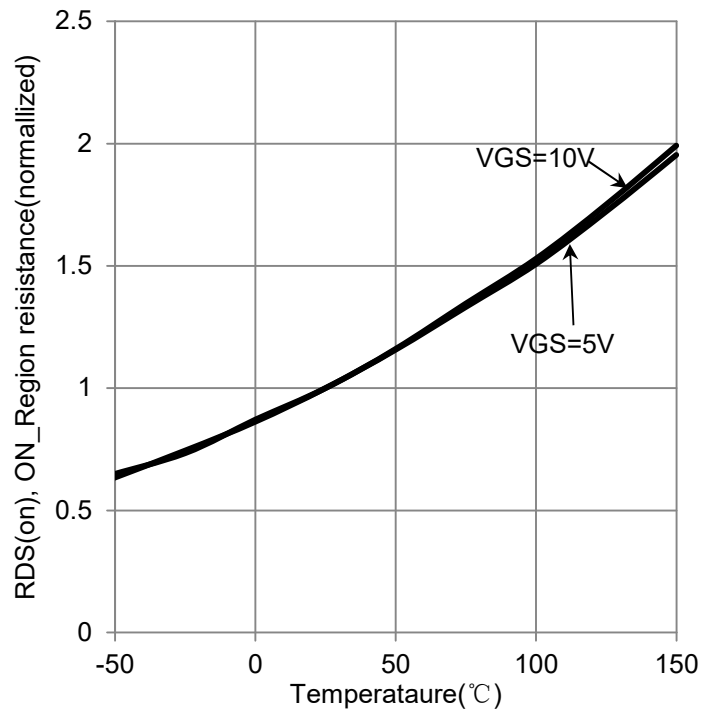
6. ELECTRICAL CHARACTERISTICS CURVES



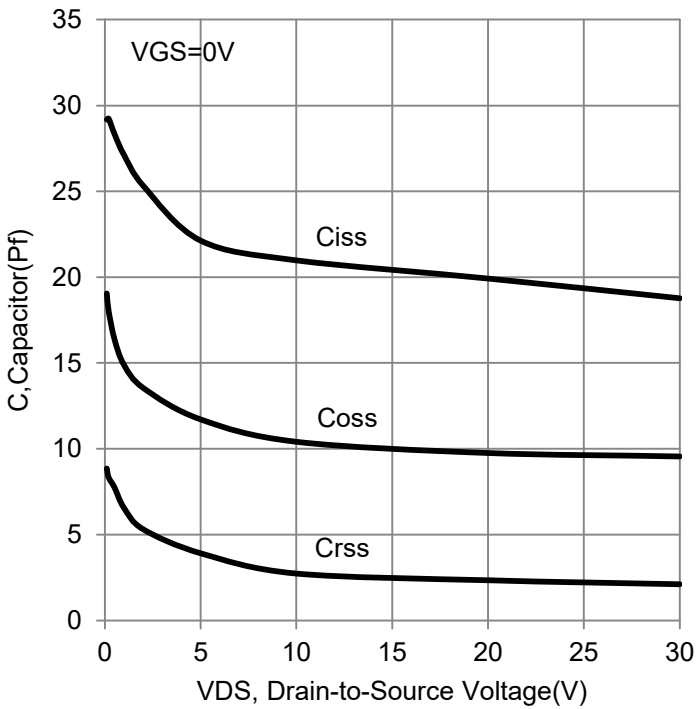
6. ELECTRICAL CHARACTERISTICS CURVES (Con.)



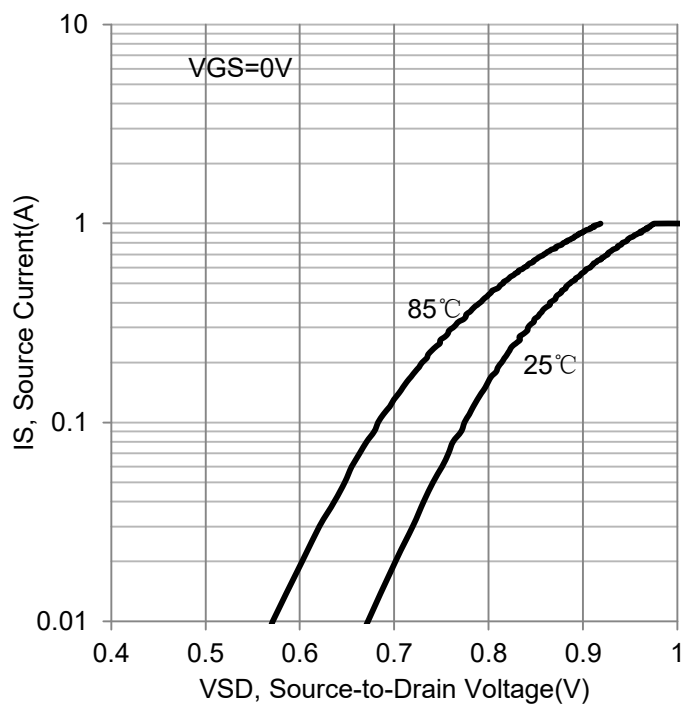
RDS(on) vs. VGS



RDS(on) vs. Temperature



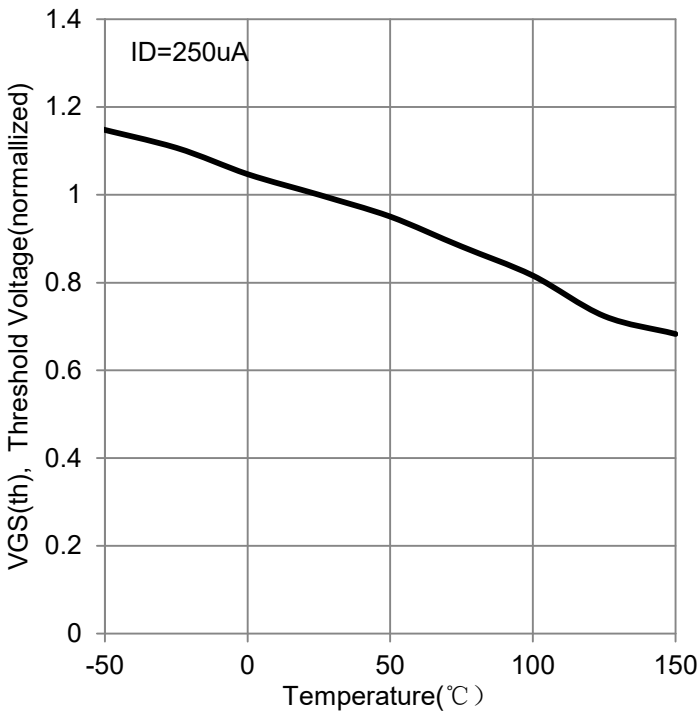
Capacitor vs. VDS



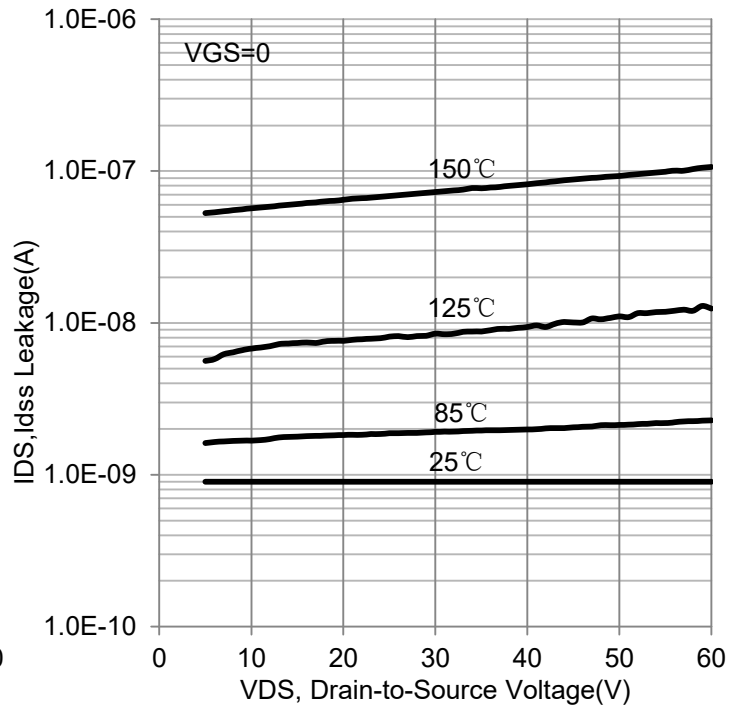
IS vs. VSD



6. ELECTRICAL CHARACTERISTICS CURVES (Con.)



VGS(th) vs. Temperature



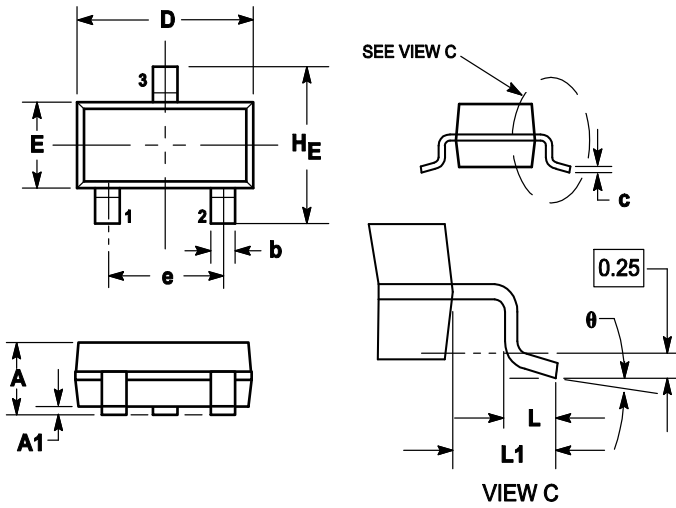
IDS vs. VDS



7. OUTLINE AND DIMENSIONS

Notes:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.



DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.89	1	1.11	0.035	0.04	0.044
A1	0.01	0.06	0.1	0.001	0.002	0.004
b	0.37	0.44	0.5	0.015	0.018	0.02
c	0.09	0.13	0.18	0.003	0.005	0.007
D	2.80	2.9	3.04	0.11	0.114	0.12
E	1.20	1.3	1.4	0.047	0.051	0.055
e	1.78	1.9	2.04	0.07	0.075	0.081
L	0.10	0.2	0.3	0.004	0.008	0.012
L1	0.35	0.54	0.69	0.014	0.021	0.029
HE	2.10	2.4	2.64	0.083	0.094	0.104
θ	0°	---	10°	0°	---	10°

8. SOLDERING FOOTPRINT

